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## NTE245 (NPN) & NTE246 (PNP) Silicon Complementary Transistors Darlington Power Amplifier

### Description:

The NTE245 (NPN) and NTE246 (PNP) are silicon complementary Darlington transistors in a TO3 type case designed for use as output devices in general purpose amplifier applications.

### Features:

- High DC Current Gain:  $h_{FE} = 4000$  Typ @  $I_C = 5A$
- Monolithic Construction with Built-In Base-Emitter Shunt Resistors

### Absolute Maximum Ratings:

Collector-Emitter Voltage, $V_{CEO}$ .....	80V
Collector-Base Voltage, $V_{CB}$ .....	80V
Emitter-Base Voltage, $V_{EB}$ .....	5V
Collector Current, $I_C$ .....	10A
Base Current, $I_B$ .....	200mA
Total Power Dissipation ( $T_C = +25^\circ C$ ), $P_D$ .....	150W
Derate Above $25^\circ C$ .....	0.857W/ $^\circ C$
Operating Junction Temperature Range, $T_J$ .....	$-55^\circ$ to $+200^\circ C$
Storage Temperature Range, $T_{stg}$ .....	$-55^\circ$ to $+200^\circ C$
Thermal Resistance, Junction-to-Case, $R_{thJC}$ .....	1.17 $^\circ C/W$

### Electrical Characteristics: ( $T_C = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>OFF Characteristics</b>						
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 100mA, I_B = 0$ , Note 1	80	-	-	V
Collector-Emitter Leakage Current	$I_{CEO}$	$V_{CE} = 40V, I_B = 0$	-	-	1.0	mA
		$V_{EB} = 80V, R_{BE} = 1k\Omega$	-	-	1.0	mA
	$V_{EB} = 80V, R_{BE} = 1k\Omega, T_C = +150^\circ C$	-	-	5.0	mA	
Emitter Cutoff Current	$I_{EBO}$	$V_{BE} = 5V, I_C = 0$	-	-	2.0	mA

Note 1. Pulse Test: Pulse Width = 300 $\mu s$ , Duty Cycle = 2%

**Electrical Characteristics (Cont'd):** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>ON Characteristics (Note 1)</b>						
DC Current Gain	$h_{FE}$	$V_{CE} = 3\text{V}, I_C = 5\text{A}$	1000	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 5\text{A}, I_B = 20\text{mA}$	–	–	2.0	V
		$I_C = 10\text{A}, I_B = 50\text{mA}$	–	–	4.0	V
Base–Emitter Voltage	$V_{BE}$	$V_{CE} = 3\text{V}, I_C = 5\text{A}$	–	–	3.0	V

Note 1. Pulse Test: Pulse Width =  $300\mu\text{s}$ , Duty Cycle = 2%

